

# AO4805

-30V P+P-Channel Enhancement Mode MOSFET

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#### **GENERAL FEATURES**

- V<sub>DS</sub> = -30V I<sub>D</sub> = -8 A
- $R_{DS(ON)} < -22m\Omega @ V_{GS} = 10 V$
- $R_{DS(ON)} < -26 \, m\Omega$  @  $V_{GS}=4.5V$

#### Package and Pin Configuration



SOP-8 top view

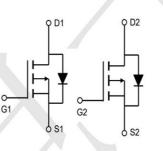
D1 D1 D2 D2 8 7 6 5 1 2 3 4 S1 G1 S2 G2 8 7 6 5 TECH PUBLIC 4805

2 3 4

#### Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

**Circuit diagram** 



#### Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>A</sub> =25℃	Continuous Drain Current <sup>3</sup>	8	А
I <sub>D</sub> @T <sub>A</sub> =70℃	Continuous Drain Current <sup>3</sup>	7	А
I <sub>DM</sub>	Pulsed Drain Current <sup>1</sup>	40	А
P <sub>D</sub> @T <sub>A</sub> =25℃	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

# Thermal Data

Symbol	Parameter		Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max.	62.5	°C/W



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# Electrical Characteristics (T\_A=25 $^\circ\!\!\!\mathrm{C}$ unless otherwise noted)

	, J					
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
$\Delta BV_{DSS} / \Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I <sub>D</sub> =1mA		0.01	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =8A		-	22	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A		-	26	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
9 <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =8A	-	8	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (Tj=25°C)	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	uA
	Drain-Source Leakage Current (Tj=70°C)	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-		25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V	-	82	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =8A	-	14.5	23	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =24V	-	2.3	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	7.7	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =15V	-	7.2	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	8.6	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω,V <sub>GS</sub> =10V	) -	24.8	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =15Ω	-	8.6	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	950	1420	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	220	. <u>-</u>	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	160	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	1	1.5	Ω

# Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =1.7A, V <sub>GS</sub> =0V	-	i.	1.2	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	I <sub>S</sub> =8A, V <sub>GS</sub> =0V,	-	25	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/µs	-	21		nC



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#### **Typical Electrical and Thermal Characteristics**

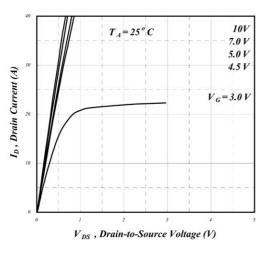


Fig 1. Typical Output Characteristics

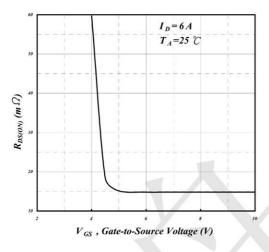


Fig 3. On-Resistance v.s. Gate Voltage

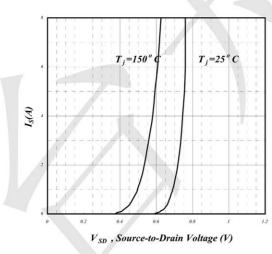


Fig 5. Forward Characteristic of Reverse Diode

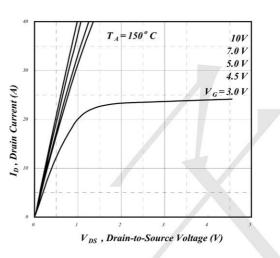


Fig 2. Typical Output Characteristics

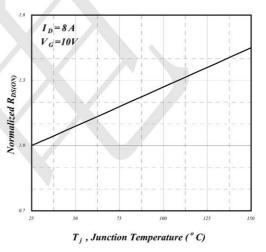


Fig 4. Normalized On-Resistance v.s. Junction Temperature

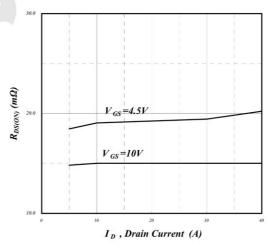


Fig 6. On-Resistance vs. Drain Current



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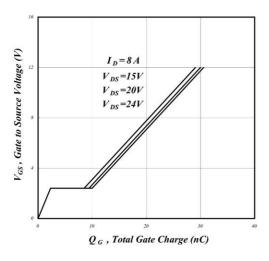


Fig 7. Gate Charge Characteristics

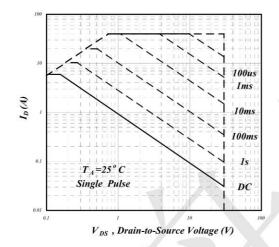


Fig 9. Maximum Safe Operating Area

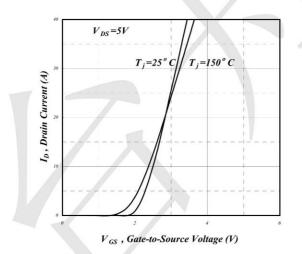


Fig 11. Transfer Characteristics

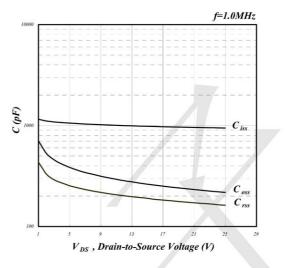
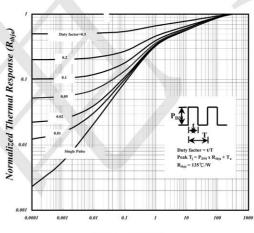


Fig 8. Typical Capacitance Characteristics



t, Pulse Width (s)

Fig 10. Effective Transient Thermal Impedance

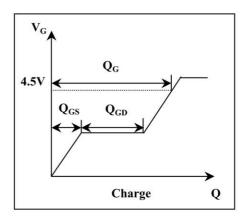


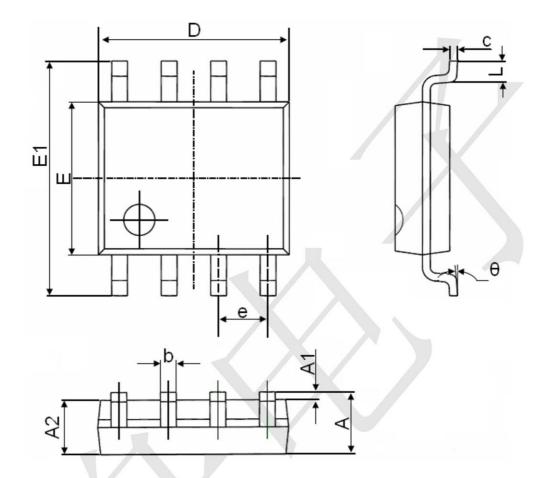
Fig 12. Gate Charge Waveform



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## **SOP-8 Package Information**



Min. 1.350	<b>Max.</b> 1.750	Min.	Max.	
	1.750	0.052		
		0.053	0.069	
0.100	0.250	0.004	0.010	
1.350	1.550	0.053	0.061	
0.330	0.510	0.013	0.020	
0.170	0.250	0.006	0.010	
4.700	5.100	0.185	0.200	
3.800	4.000	0.150	0.157	
5.800	6.200	0.228	0.244	
1.270(BSC)		0.050(I	BSC)	
0.400	1.270	0.016	0.050	
0°	8°	0°	8°	
	0.330 0.170 4.700 3.800 5.800 1.270 0.400	0.330         0.510           0.170         0.250           4.700         5.100           3.800         4.000           5.800         6.200           1.270(BSC)         0.400	0.330         0.510         0.013           0.170         0.250         0.006           4.700         5.100         0.185           3.800         4.000         0.150           5.800         6.200         0.228           1.270(BSC)         0.016	

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